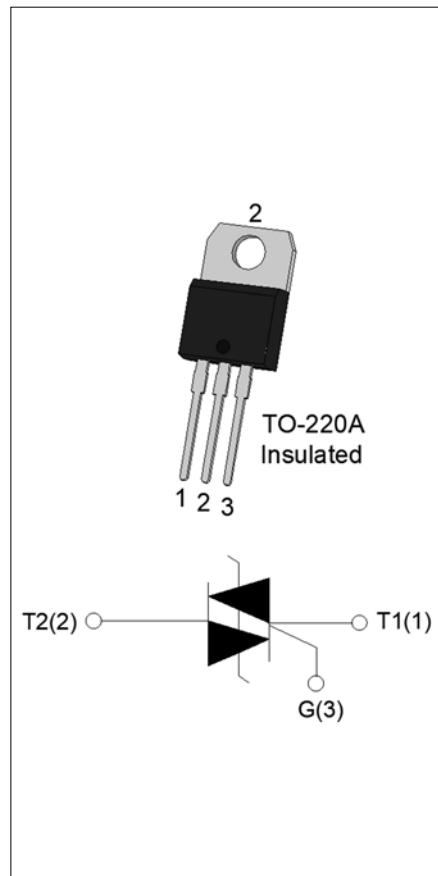


**DESCRIPTION:**

The ACJT825-8A triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The ACJT825-8A embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. By using an internal ceramic pad, ACJT825-8A provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_T(\text{RMS})$	8	A
$V_{\text{DRM}} / V_{\text{RRM}}$	800	V
$I_{\text{GT I/II/III}}$	25/25/25	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{\text{stg}}$	-40-150	°C
Operating junction temperature range	$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{\text{DRM}}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{\text{RRM}}$	800	V
RMS on-state current ( $T_c \leqslant 98^\circ\text{C}$ )	$I_T(\text{RMS})$	8	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{\text{SM}}$	80	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		88	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	32	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{\text{GT}}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	$dI/dt$	100	$\text{A}/\mu\text{s}$
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )	$I_{\text{GM}}$	4	A

Average gate power dissipation ( $T_j=125^\circ\text{C}$ )	$P_{G(AV)}$	0.5	W
Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25^\circ\text{C}$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	2.5	kV

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12\text{V}$ $R_L=33\Omega$	I - II - III	MAX.	25	mA
$V_{GT}$		I - II - III	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{k}\Omega$	I - II - III	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I - III	MAX.	35	mA
		II		55	
$I_H$	$I_T=100\text{mA}$		MAX.	30	mA
$dV/dt$	$V_D=540\text{V}$ Gate Open $T_j=125^\circ\text{C}$		MIN.	2500	V/ $\mu\text{s}$
$(dI/dt)c$	$(dV/dt)c=10\text{V}/\mu\text{s}$ , $T_j=125^\circ\text{C}$		MIN.	8	A/ms
$t_{on}$	$I_G=40\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^\circ\text{C}$	TYP.	3	$\mu\text{s}$	
$t_{off}$			30		
$V_{CL}$	$I_{CL}=0.1\text{mA}$ $t_p=1\text{ms}$		MIN.	850	V

**STATIC CHARACTERISTICS**

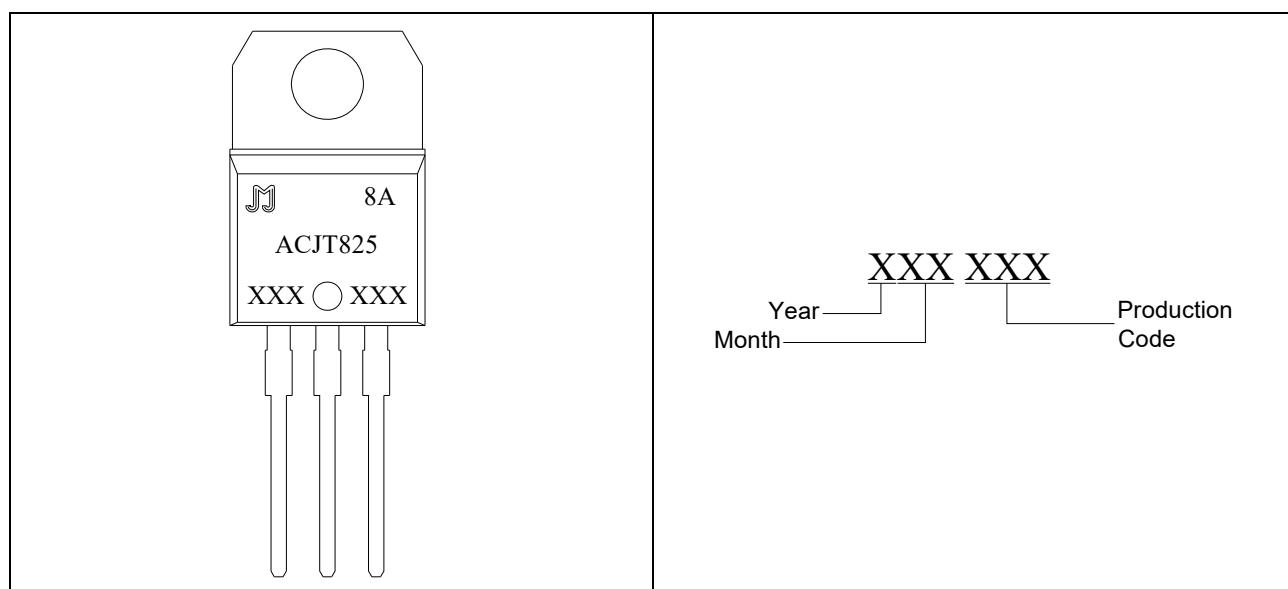
Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=10\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.4	V
$V_{TO}$	Threshold voltage	$T_j=125^\circ\text{C}$	0.78	V
$R_D$	Dynamic resistance	$T_j=125^\circ\text{C}$	38	$\text{m}\Omega$
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	$\mu\text{A}$
$I_{RRM}$		$T_j=125^\circ\text{C}$	0.5	mA

**THERMAL RESISTANCES**

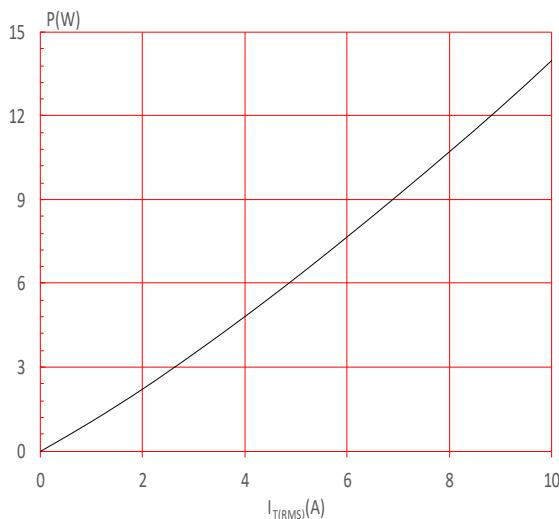
Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.5	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^\circ\text{C}/\text{W}$

**ORDERING INFORMATION**

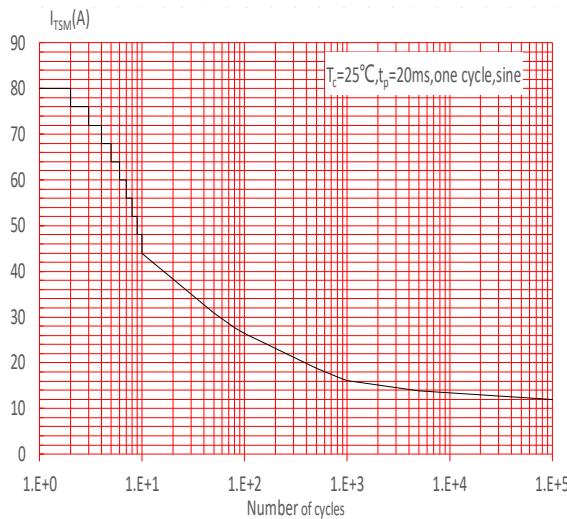
<b>AC</b>	<b>J</b>	<b>T</b>	<b>8</b>	<b>25</b>	<b>-8</b>	<b>A</b>
<u>AC switch</u>						
<u>JieJie Microelectronics Co.,Ltd.</u>						
		<u>Triacs</u>				
			<u><math>I_{T(RMS)}:8A</math></u>			
<u><math>25: I_{GT1-3} \leq 25mA</math></u>						<u><math>8: V_{DRM} / V_{RRM} \geq 800V</math></u>

**MARKING**

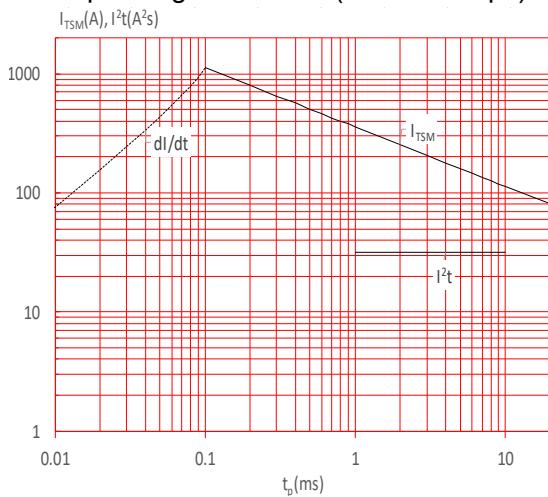
**FIG.1** Maximum power dissipation versus RMS on-state current



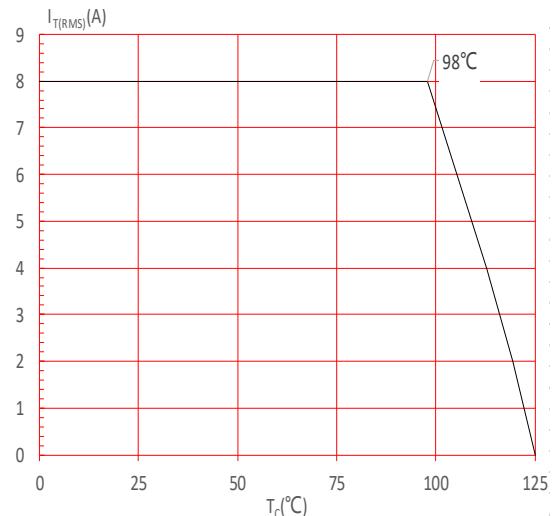
**FIG.3:** Surge peak on-state current versus number of cycles



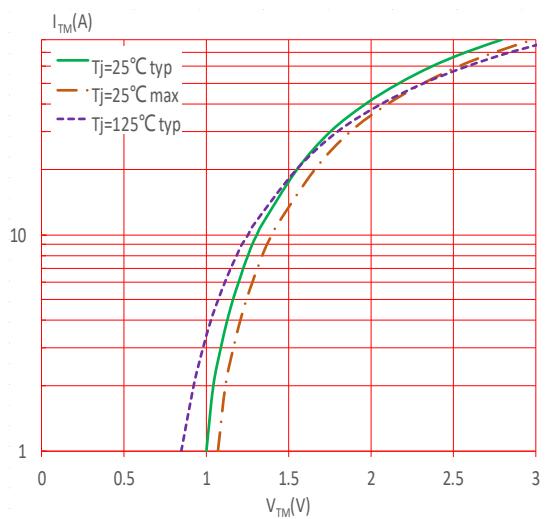
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $dI/dt < 100\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

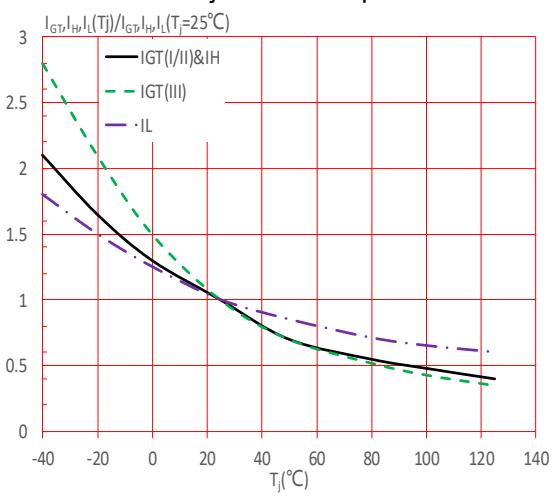
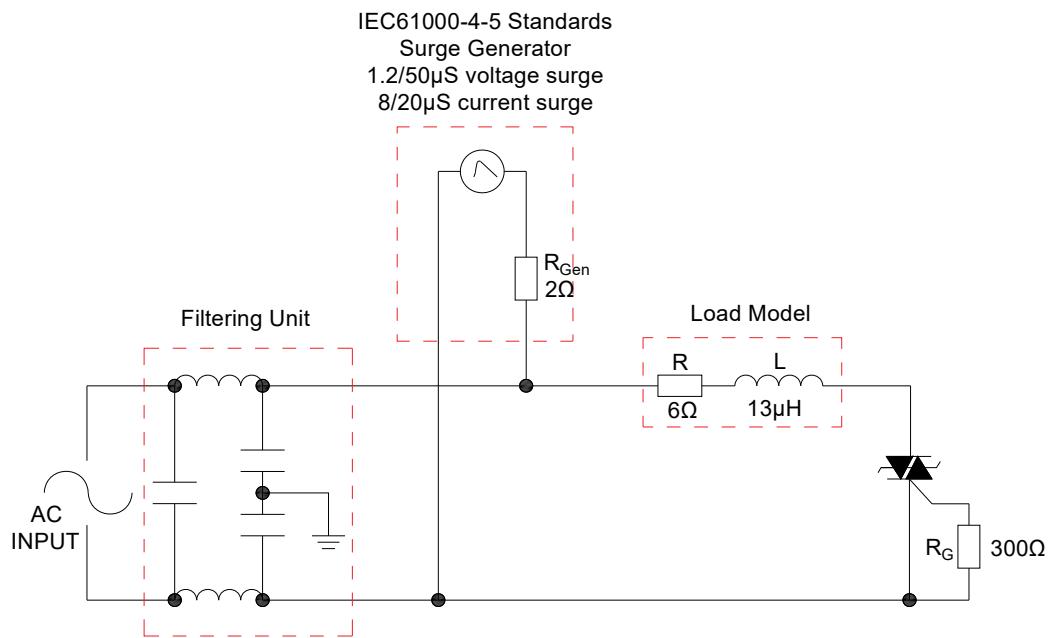


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie

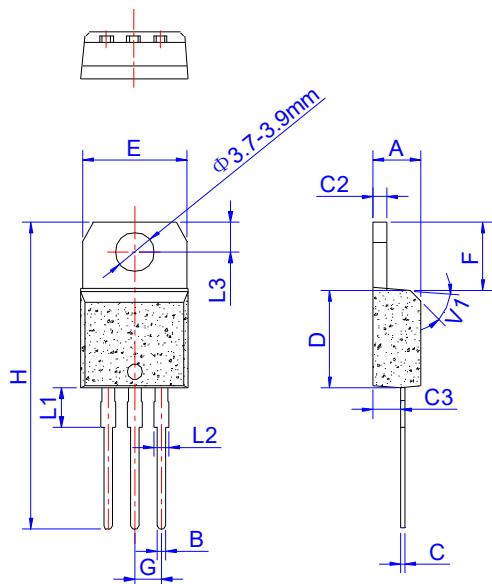
## ORDERING INFORMATION

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJT825-8A	800	25	TO-220A(Ins)	50	Tube

## Document Revision History

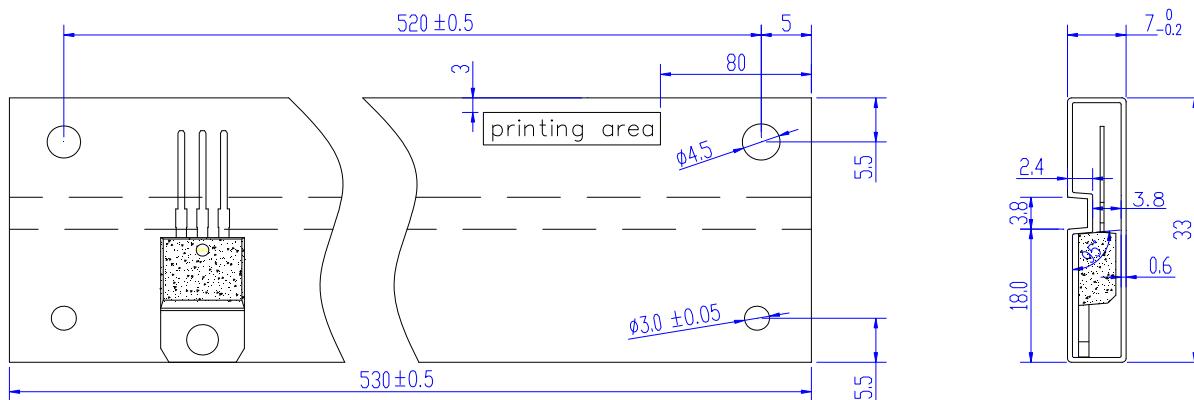
Date	Revision	Changes
Apr.13, 2023	A.1.0	Last updated

## PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.25		6.85	0.246		0.270
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	3.45		4.05	0.136		0.159
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

## DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220A	TUBE	50	1,000	5,000

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